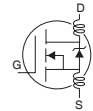


Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	40	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.039	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.0035	0.004	Ω	$V_{GS} = 10V, I_D = 121A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = 10V, I_D = 250\mu A$
g_{fs}	Forward Transconductance	76	—	—	S	$V_{DS} = 25V, I_D = 121A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 40V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 32V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$
Q_g	Total Gate Charge	—	131	196	nC	$I_D = 121A$
Q_{gs}	Gate-to-Source Charge	—	36	—		$V_{DS} = 32V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	37	56		$V_{GS} = 10V$ ④
$t_{d(on)}$	Turn-On Delay Time	—	17	—	ns	$V_{DD} = 20V$
t_r	Rise Time	—	190	—		$I_D = 121A$
$t_{d(off)}$	Turn-Off Delay Time	—	46	—		$R_G = 2.5\Omega$
t_f	Fall Time	—	33	—		$R_D = 0.2\Omega$ ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	5669	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	1659	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	223	—		$f = 1.0MHz$, See Fig. 5
C_{oss}	Output Capacitance	—	6205	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
C_{oss}	Output Capacitance	—	1467	—		$V_{GS} = 0V, V_{DS} = 32V, f = 1.0MHz$
$C_{oss \text{ eff.}}$	Effective Output Capacitance ⑤	—	2249	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 32V$



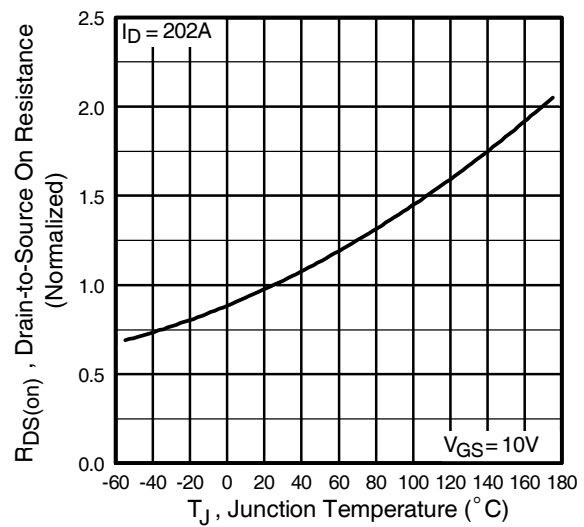
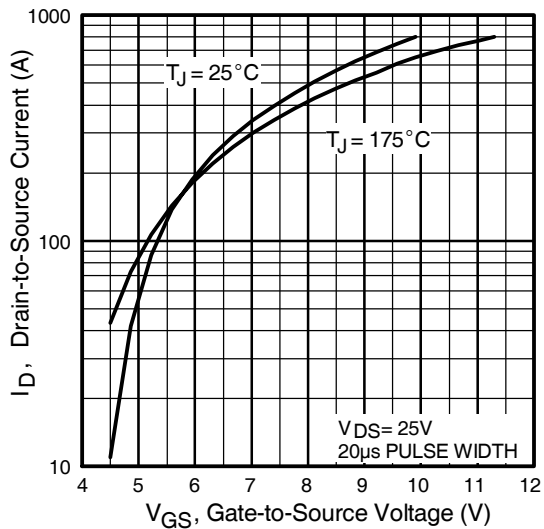
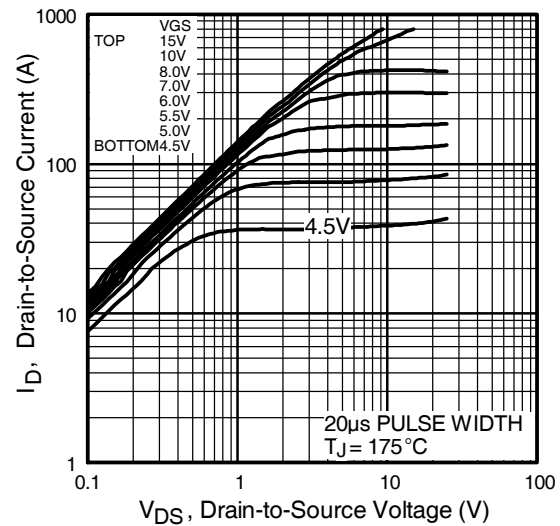
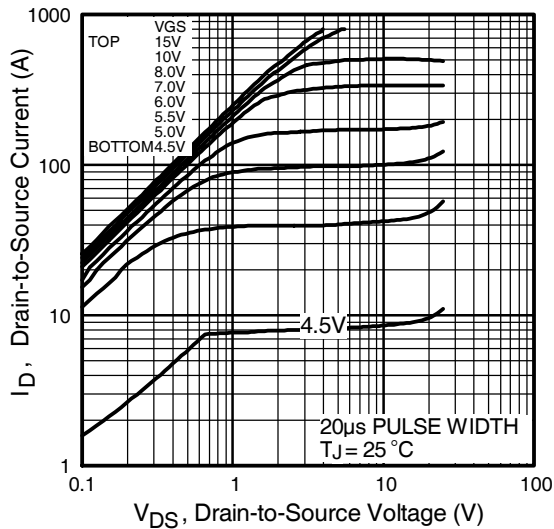
Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	202	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	808		
V_{SD}	Diode Forward Voltage	—	—	1.5	V	$T_J = 25^\circ\text{C}, I_S = 121A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	78	117	ns	$T_J = 25^\circ\text{C}, I_F = 121A$
Q_{rr}	Reverse Recovery Charge	—	163	245	nC	$di/dt = 100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 85\mu H$
 $R_G = 25\Omega$, $I_{AS} = 121A$. (See Figure 12)
- ③ $I_{SD} \leq 121A$, $di/dt \leq 130A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$,
 $T_J \leq 175^\circ\text{C}$

- ④ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ⑤ $C_{oss \text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}
- ⑥ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 75A.



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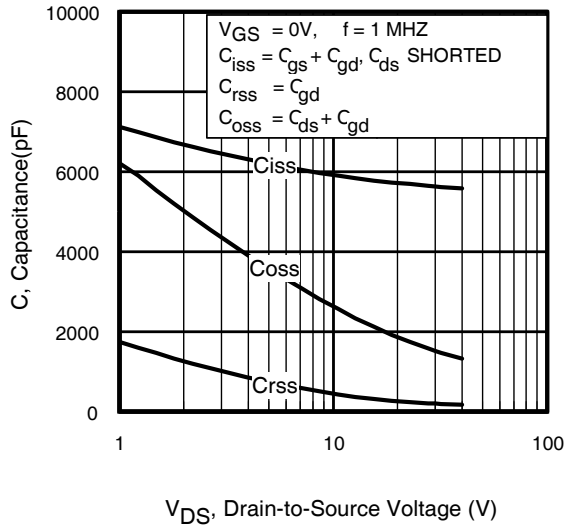


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

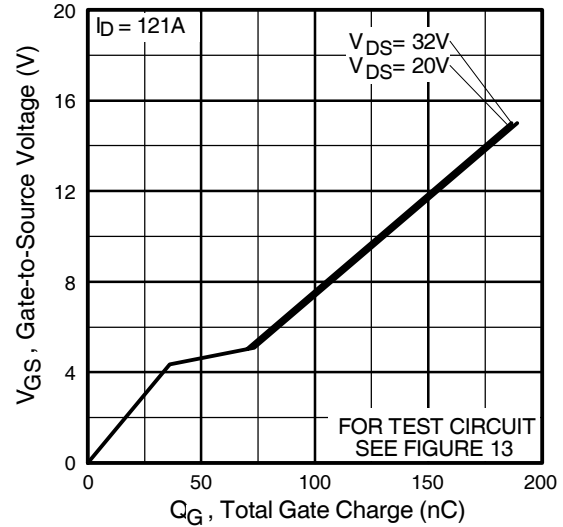


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

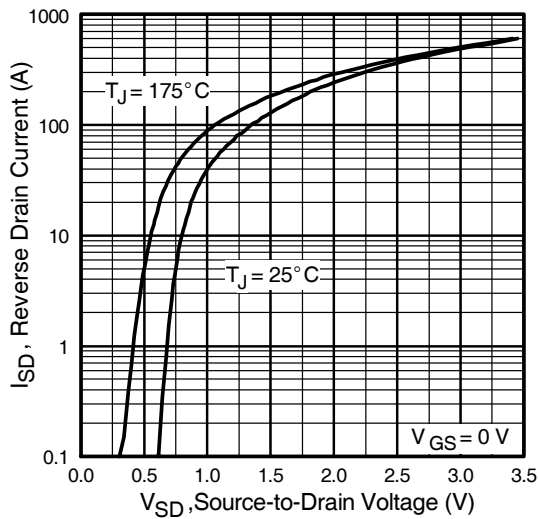


Fig 7. Typical Source-Drain Diode Forward Voltage

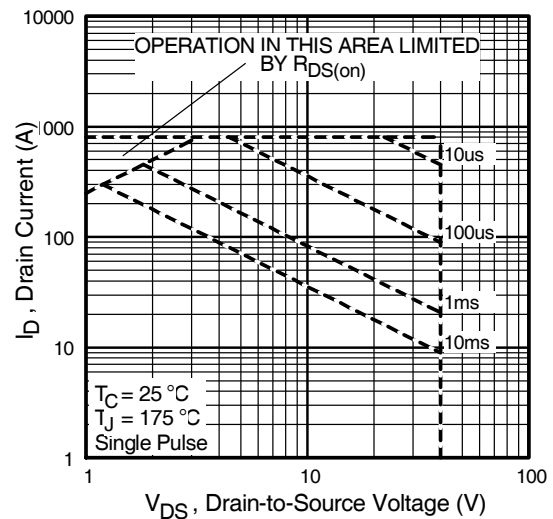


Fig 8. Maximum Safe Operating Area

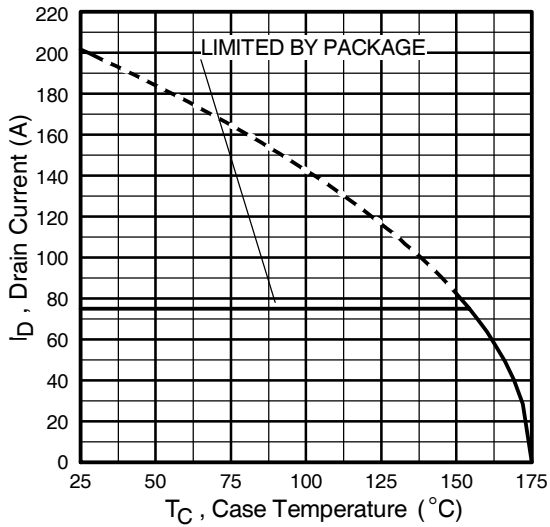


Fig 9. Maximum Drain Current Vs. Case Temperature

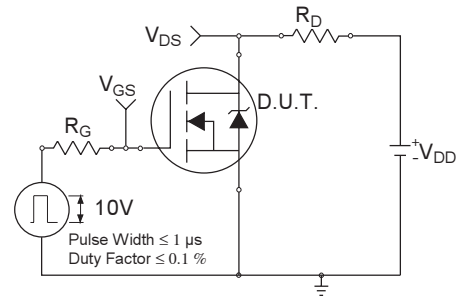


Fig 10a. Switching Time Test Circuit

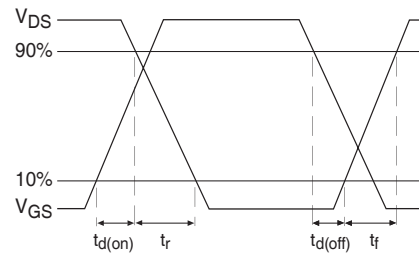


Fig 10b. Switching Time Waveforms

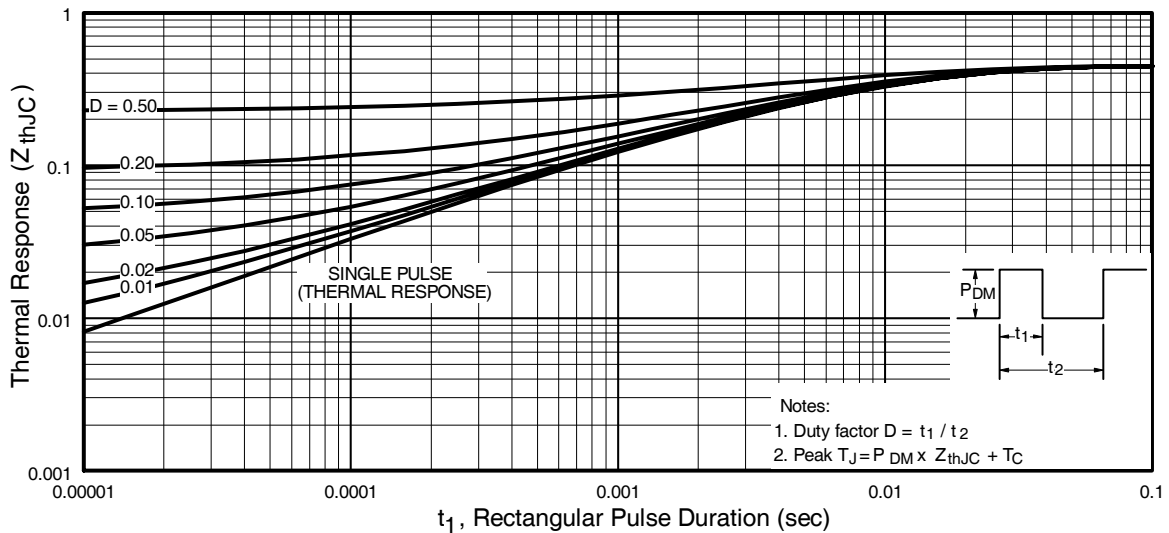


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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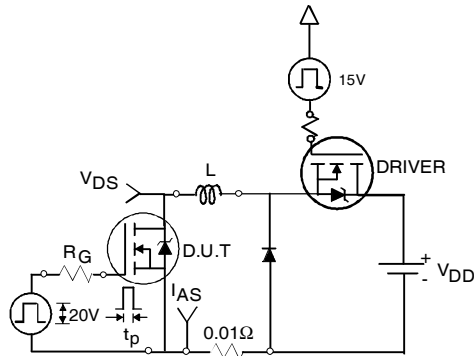


Fig 12a. Unclamped Inductive Test Circuit

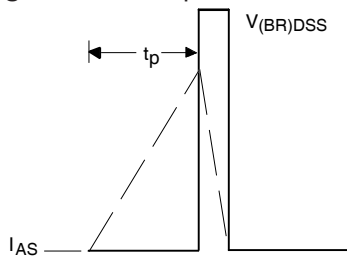


Fig 12b. Unclamped Inductive Waveforms

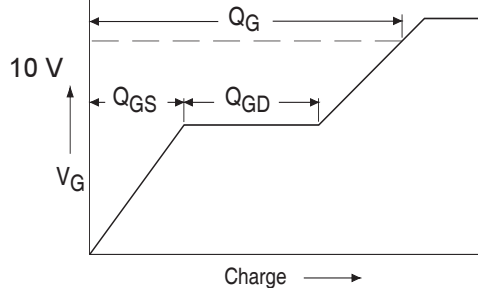


Fig 13a. Basic Gate Charge Waveform

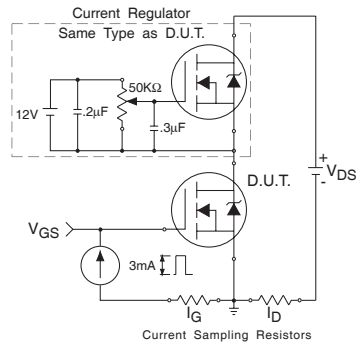


Fig 13b. Gate Charge Test Circuit

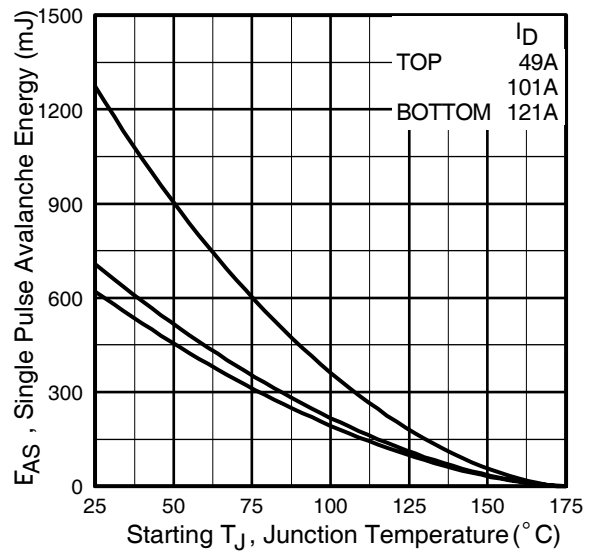


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

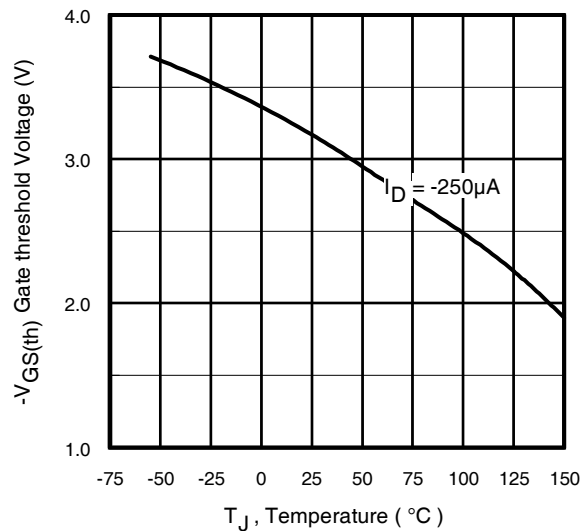


Fig 14. Threshold Voltage Vs. Temperature

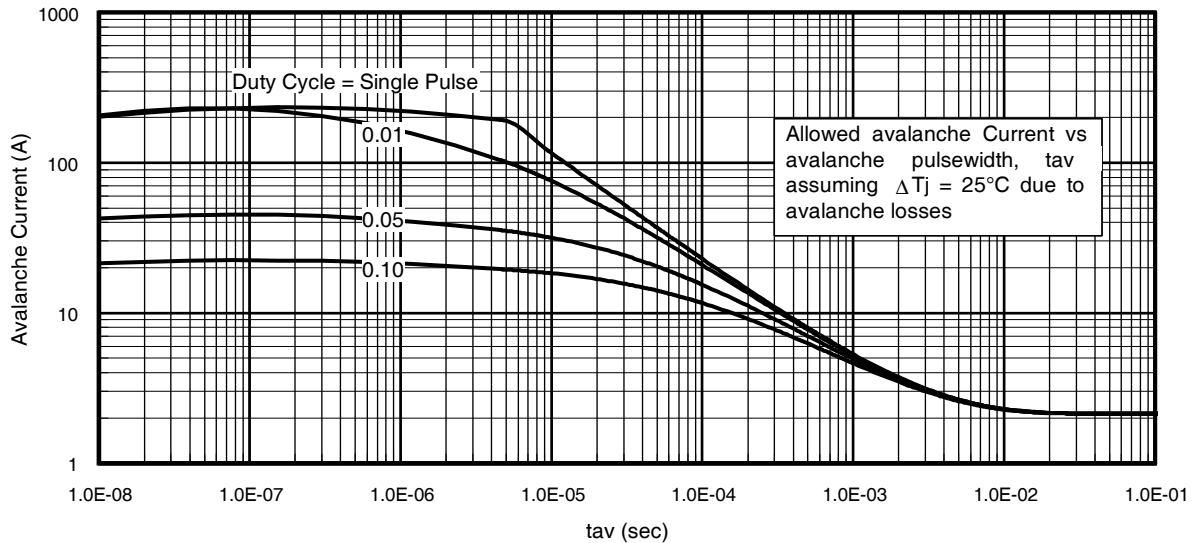


Fig 15. Typical Avalanche Current Vs. Pulsewidth

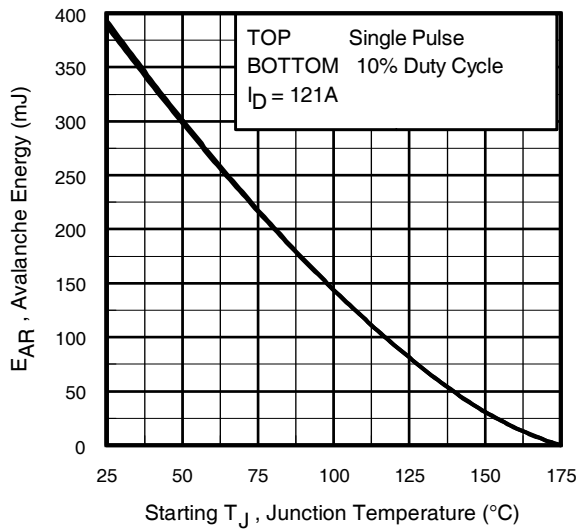


Fig 16. Maximum Avalanche Energy Vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see figure 11)

$$P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$

Peak Diode Recovery dv/dt Test Circuit

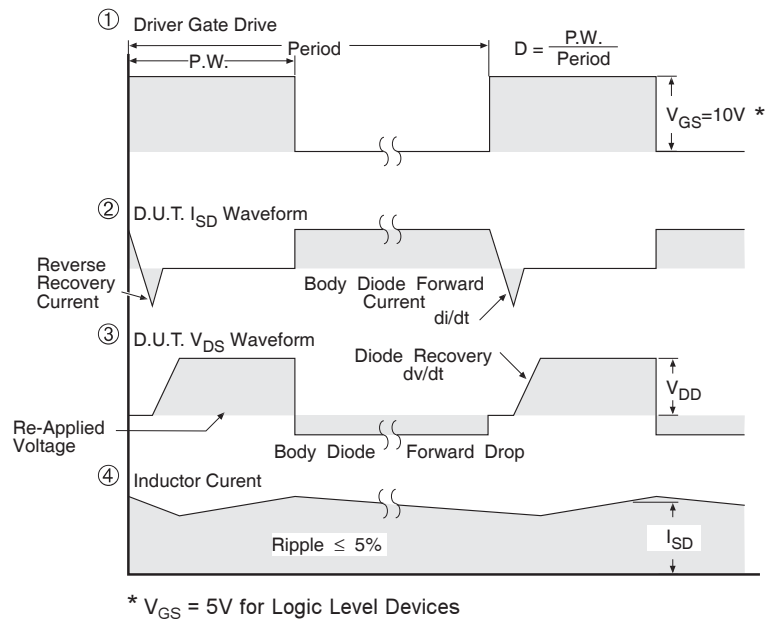
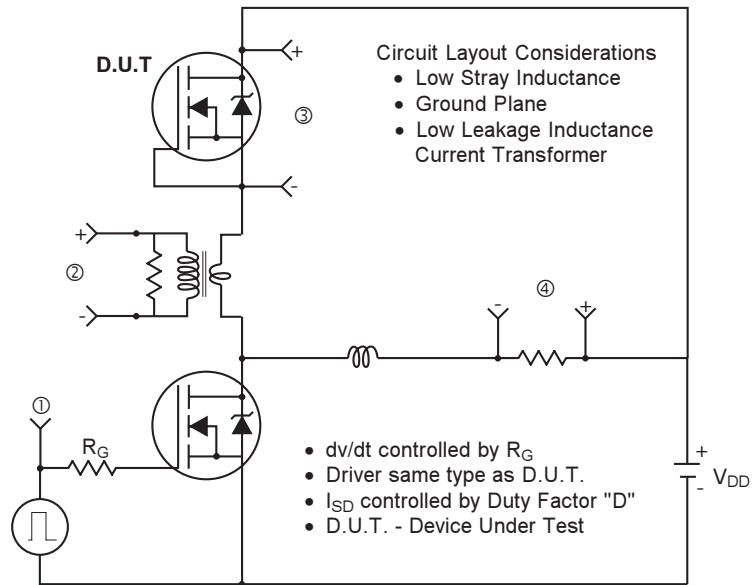
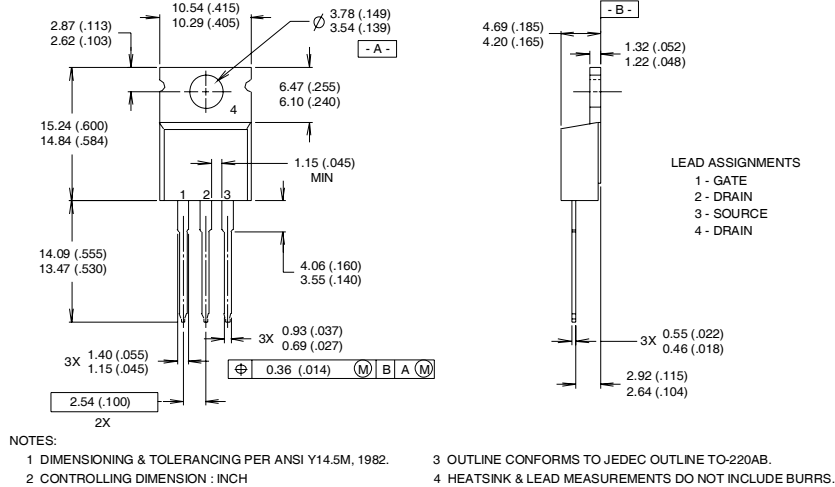


Fig 17. For N-channel HEXFET® Power MOSFETs

TO-220AB Package Outline

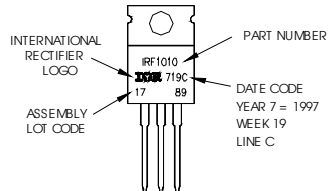
Dimensions are shown in millimeters



TO-220AB Part Marking Information

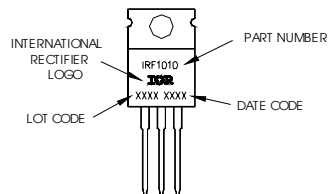
EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW/19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"



For GB Production

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW/19, 1997
IN THE ASSEMBLY LINE "C"



TO-220AB package is not recommended for Surface Mount Application.

Data and specifications subject to change without notice.
This product has been designed and qualified for the automotive [Q101] market.
Qualification Standards can be found on IR's Web site.

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Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>